

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A semiconductor device for transmitting a signal of high frequency of several GHz or more, the semiconductor device comprising:

regions for forming a plurality of functional blocks;

a region for forming wiring layers for connecting the functional blocks,

wherein each of the regions for forming the functional blocks includes a multilayer wiring, [[and]]

wherein the region for forming the wiring layers for connecting adjacent functional blocks includes a coaxial line comprising an inner signal line for transmitting the signal of high frequency of several GHz or more, and an outer ground line surrounding the signal line via an insulating film as viewed cross sectionally, so that the inner signal line and outer ground line have a common axis along at least a portion of a length of the coaxial line, and

wherein the region for forming the plurality of functional blocks and the region for forming the wiring layers for connecting adjacent functional blocks are each formed on a semiconductor substrate.

2. (Previously presented) A semiconductor device according to claim 1, wherein a bottom surface of a wiring in the multilayer wiring provided in the region for forming the functional block is on the same plane as a bottom surface of the coaxial line provided in the region for forming the wiring layers for connecting the functional blocks.

3. (Currently amended) A semiconductor device for transmitting a signal of high frequency of several GHz or more, the semiconductor device comprising:

regions for forming a plurality of functional blocks; and

a region for forming wiring layers for connecting the functional blocks,

wherein each of the regions for forming the functional blocks includes a multilayer wiring, and the region for forming the wiring layers for connecting the functional blocks includes a transmission line comprising a signal line for transmitting the signal of high frequency of several GHz or more, and ground lines and/or power source lines formed above and below the signal line, respectively, as viewed cross sectionally, to sandwich the signal line via an insulating film, and

wherein the region for forming the plurality of functional blocks and the region for forming the wiring layers for connecting adjacent functional blocks are each formed on a semiconductor substrate.

4. (Previously presented) A semiconductor device according to claim 3, wherein a bottom surface of a wiring layer in the multilayer wiring provided in the region for

forming the functional block is on the same plane as a bottom surface of the ground line or power source line located below the transmission line provided in the region for forming the wiring layers for connecting the functional blocks.

5. (Currently amended) A semiconductor device for transmitting a signal of high frequency of several GHz or more, the semiconductor device comprising:

regions for forming a plurality of functional blocks;

a region for forming wiring layers for connecting the functional blocks,

wherein each of the regions for forming the functional blocks includes a multilayer wiring, and

wherein the region for forming the wiring layers for connecting the functional blocks includes wiring layers thicker than those in the functional blocks, and a bottom surface of a wiring layer in the multilayer wiring provided in the region for forming the functional block is on the same plane as a bottom surface of the wiring layer provided in the region for forming the wiring layers for connecting the functional blocks as viewed cross sectionally, and

wherein the region for forming the plurality of functional blocks and the region for forming the wiring layers for connecting adjacent functional blocks are each formed on a semiconductor substrate.

6-9. (Canceled)

10. (Previously presented) The semiconductor device of claim 1, wherein the inner signal line of the coaxial line has a thickness greater than a thickness of wiring layers in the functional blocks.

11. (Previously presented) The semiconductor device of claim 3, wherein the signal line has a thickness greater than a thickness of wiring layers in the functional blocks.

12. (New) The semiconductor device of claim 1, wherein the wiring layer, the multilayer wiring and the signal line are formed by a CMP method and a damascene method.

13. (New) The semiconductor device of claim 3, wherein the wiring layer, the multilayer wiring, the signal line, and the ground lines or the power source lines are formed by a CMP method or a damascene method.

14. (New) The semiconductor device of claim 5, wherein the wiring layer and the multilayer wiring are formed by a CMP method or a damascene method.